

Search History (9pp) 6/12/05

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|-------|--|--|------------------|---------|------------------|
| L1 | 8 | source near6 common adj:ground and memory adj:array.ti. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 20:11 |
| L2 | 31389 | CD-ROM and Dvd | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 20:12 |
| L3 | 2 | CD-ROM and Dvd and memory adj:array and laser adj:diode | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 20:13 |
| L4 | 2 | "5696714".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 20:13 |
| L5 | 5611 | ((257/79) or (257/88) or (257/93) or (257/99) or (257/499) or (257/501) or (257/678) or (257/687) or (257/905) or (257/906) or (257/911)).CCLS. | US-PGPUB; USPAT | OR | OFF | 2005/06/12 20:40 |
| L6 | 0 | I5 and (planari?ation planari?e) and (Si silicon semiconductor) adj thin adj film and (integrated adj circuit IC) adj2 (layer) and (light-emitting light adj emitting laser adj diode photodiode photodetect\$3 hall adj sensor) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/12 20:42 |
| S1 | 4 | "743104".ap. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/12 13:38 |
| S2 | 1 | (US-20040135157-\$).did. | US-PGPUB | OR | OFF | 2005/05/24 11:53 |
| S3 | 0 | jp-60206889\$-.did. | US-PGPUB | OR | OFF | 2005/05/24 11:54 |
| S4 | 1 | jp-60206889\$-.did. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/05/24 11:58 |

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| S5 | 2 | jp-10063807\$\$ did. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/05/24 11:58 |
| S6 | 152 | (257/93).CCLS. | US-PGPUB; USPAT | OR | OFF | 2005/06/11 19:50 |
| S7 | 209 | (257/501).CCLS. | US-PGPUB; USPAT | OR | OFF | 2005/06/11 19:50 |
| S8 | 360 | S6-S7 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/11 19:51 |
| S9 | 127 | S8 and (light adj emitting light-emitting) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/11 19:51 |
| S10 | 1 | S8 and (light adj emitting light-emitting) and (("without" "no") adj wire adj bond\$3) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 19:54 |
| S11 | 127 | S8 and (light adj emitting light-emitting) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 19:54 |
| S12 | 34 | S8 and (light adj emitting light-emitting) and planar\$5 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 19:54 |
| S13 | 14 | (US-6773943-\$ or US-6692845-\$ or US-6472718-\$ or US-6403985-\$ or US-6339233-\$ or US-6114715-\$ or US-5955747-\$ or US-5866922-\$ or US-5663581-\$ or US-5115284-\$ or US-4984035-\$ or US-4956683-\$ or US-4335501-\$ or US-T979005-\$).did. | USPAT | OR | OFF | 2005/06/11 20:11 |
| S14 | 4 | S13 and print\$3 | US-PGPUB; USPAT | OR | OFF | 2005/06/11 20:33 |
| S15 | 5349 | ((257/79) or (257/88) or (257/93) or (257/99) or (257/499) or (257/501) or (257/678) or (257/687)).CCLS. | US-PGPUB; USPAT | OR | OFF | 2005/06/12 20:40 |

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| S16 | 1 | S15 and monolithic and substrate near6 integrated adj circuit and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/11 20:39 |
| S17 | 2 | S15 and substrate near6 integrated adj circuit and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/11 20:43 |
| S18 | 0 | S15 and monolithic and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/11 20:43 |
| S19 | 3 | S15 and monolithic and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/11 20:45 |
| S20 | 3 | S15 and integrated adj circuit near6 substrate and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/11 20:46 |
| S21 | 2 | S15 and integrated adj circuit near6 (semiconductor silicon) near4 substrate and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/11 20:47 |
| S22 | 2 | S15 and (IC integrated adj circuit) near6 (semiconductor silicon) near4 substrate and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/11 20:48 |
| S23 | 17 | (IC integrated adj circuit) near6 (semiconductor silicon) near4 substrate and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) near2 array and thin adj2 film | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/11 20:55 |
| S24 | 154 | (IC integrated adj circuit) near6 (semiconductor silicon) near4 substrate and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) and thin adj2 film | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/11 21:04 |

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| S25 | 2 | ("5055907").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/11 21:26 |
| S26 | 2 | ("4755866").PN. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/11 21:30 |
| S27 | 6922 | (light-emitting light adj emitting LED laser diode) adj array and (integrated adj circuit\$2 IC monolithic\$4) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 21:31 |
| S28 | 378 | (light-emitting light adj emitting LED laser diode) adj array and (integrated adj circuit\$2 IC monolithic\$4) and planariz\$5 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 21:38 |
| S29 | 189 | (light-emitting light adj emitting LED laser adj diode) adj array and (integrated adj circuit\$2 IC monolithic\$4) and planariz\$5 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 23:22 |
| S30 | 249 | semi-insulating adj substrate.ti. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 23:23 |
| S31 | 249 | semi-insulating adj substrate.ti. and semi-insulating | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 23:27 |
| S32 | 3 | semi-insulating adj substrate.ti. and semi-insulating near6 defined | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 23:33 |
| S33 | 0 | (silicon semiconductor semi-insulating) adj substrate near4 "having" near4 (driver integrated) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 23:35 |
| S34 | 0 | (silicon semiconductor semi-insulating) adj substrate near4 "wherein" near4 (driver integrated) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 23:35 |

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| S35 | 0 | (silicon semiconductor semi-insulating) adj substrate near10 "wherein" near4 (driver integrated IC) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 23:36 |
| S36 | 0 | (silicon semiconductor semi-insulating) adj substrate near10 "wherein" near10 (driver integrated IC) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 23:36 |
| S37 | 1481 | (silicon semiconductor semi-insulating) adj substrate near10 ("in which" "wherein" "having" "within") near10 (driver integrated IC) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 23:36 |
| S38 | 72 | (silicon semiconductor semi-insulating) adj substrate near10 ("in which" "wherein" "having" "within") near10 (driver integrated IC) and planariz\$5 and (LED light-emitting light adj emitting laser adj diode) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 23:51 |
| S39 | 4756 | (silicon semiconductor) adj substrate and thin adj2 film and passivation and (integrated adj circuit IC) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 23:52 |
| S40 | 3231 | (silicon semiconductor) adj substrate and thin adj2 film and passivation and (integrated adj circuit IC) and "257"/\$7.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 23:53 |
| S41 | 444 | (silicon semiconductor) adj substrate and thin adj2 film and passivation adj (layer film) near6 substrate and (integrated adj circuit IC) and "257"/\$7.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/11 23:56 |
| S42 | 317 | (silicon semiconductor) adj substrate and thin adj2 film and passivation adj (layer film) near6 substrate and (integrated adj circuit IC) and "257"/\$7.ccls. | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 00:02 |
| S43 | 54 | (silicon semiconductor) adj substrate and thin adj2 film and planariz\$5 adj (layer film) near6 substrate and (integrated adj circuit IC) and "257"/\$7.ccls. | USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 00:02 |
| S44 | 2 | "5492851".pn. and semiconductor | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/12 15:03 |

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| S45 | 2 | "4902637".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/12 16:20 |
| S46 | 0 | (integrated adj circuit adj layer IC adj layer) and (planari?ation planari?e) and (light-emitting light adj emitting diode) adj array | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/12 15:11 |
| S47 | 0 | (integrated adj circuit adj layer IC adj layer) and (planari?ation planari?e) and (thin adj2 film light-emitting light adj emitting diode) adj array | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/12 15:12 |
| S48 | 79 | (integrated adj circuit adj layer IC adj layer) and (planari?ation planari?e) and (thin adj2 film light-emitting light adj emitting diode) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/12 15:22 |
| S49 | 15 | (US-20050087817-\$ or US-20040155302-\$ or US-20040155301-\$ or US-20040016976-\$ or US-20040012053-\$ or US-20040007746-\$ or US-20030067043-\$).did. or (US-6903427-\$ or US-6861715-\$ or US-6812488-\$ or US-6717222-\$ or US-6706546-\$ or US-6690845-\$ or US-6684007-\$ or US-6611635-\$).did. | US-PGPUB; USPAT | OR | OFF | 2005/06/12 15:22 |
| S50 | 4 | S49 and thin adj film near5 planariz\$5 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/12 15:57 |
| S51 | 0 | S49 and thin adj film near5 planariz\$5 and integrated adj circuit adj layer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/12 15:25 |
| S52 | 4 | S49 and thin adj film near5 planariz\$5 and (IC adj layer integrated adj circuit adj layer) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 15:28 |
| S53 | 4 | S49 and thin adj film near5 planariz\$5 and (IC adj layer integrated adj circuit adj layer) and thin adj film adj device | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 15:45 |

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| S54 | 4 | S49 and thin adj film near5 planariz\$5 and (IC adj layer integrated adj circuit adj layer) and thin adj film adj device and IC adj chip adj layer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 15:50 |
| S55 | 0 | S49 and thin adj film near5 planariz\$5 and (IC adj layer integrated adj circuit adj layer) and thin adj film adj device and IC adj chip adj layer and vcsel adj layer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 15:51 |
| S56 | 4 | S49 and thin adj film near5 planariz\$5 and (IC adj layer integrated adj circuit adj layer) and thin adj film adj device and IC adj chip adj layer and device adj layer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 15:52 |
| S57 | 4 | S49 and thin adj film near5 planariz\$5 and (IC adj layer integrated adj circuit adj layer) and thin adj film adj device and IC adj chip adj layer and device adj layer and (planari?e planari?ation) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 15:53 |
| S58 | 15 | S49 and planariz\$5 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/12 15:58 |
| S59 | 0 | S49 and planariz\$5 and integrated adj circuit adj layer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/06/12 15:58 |
| S60 | 15 | S49 and planariz\$5 and (IC integrated adj circuit) adj2 layer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 15:58 |
| S61 | 15 | S49 and planariz\$5 and (IC integrated adj circuit) adj2 layer and thin adj film | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 16:00 |
| S62 | 4 | S49 and planariz\$5 and (IC integrated adj circuit) adj2 layer and thin adj film and (light-emitting light adj emitting vcsel) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 16:00 |

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| S63 | 4 | S49 and planariz\$5 and (IC integrated adj circuit) adj2 layer and thin adj film and (light-emitting light adj emitting vcsel piezoelectric hall) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 16:01 |
| S64 | 4 | S49 and planariz\$5 and (IC integrated adj circuit) adj2 layer and thin adj film and (light-emitting light adj emitting vcsel piezoelectric hall laser adj diode photodetect\$3 photodiode) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 16:01 |
| S65 | 15 | IC adj layer near6 stack\$3 and (planari?ation planari?e) and (EO LED light-emitting light adj emitting laser diode vcsel photodiode photodetect\$3 hall adj sensor piezo-electric piezoelectric) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 17:24 |
| S66 | 29 | cd-rom near4 diode | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 18:37 |
| S67 | 5991 | memory adj device and memory adj cell adj array and ((semiconductor silicon) adj substrate) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 17:25 |
| S68 | 2403 | memory adj device and memory adj cell adj array.ti,ab,clm. and ((semiconductor silicon) adj substrate) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 17:25 |
| S69 | 1206 | memory adj device and memory adj cell adj array.ti,ab,clm. and ((semiconductor silicon) adj substrate).ti,ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 17:25 |
| S70 | 687 | memory adj device and memory adj cell adj array.ti,ab,clm. and ((semiconductor silicon) adj substrate).ti,ab,clm. | USPAT | OR | ON | 2005/06/12 17:26 |
| S71 | 0 | memory adj device and memory adj cell adj array.ti,ab,clm. and ((GaAs) adj substrate).ti,ab,clm. | USPAT | OR | ON | 2005/06/12 17:26 |
| S72 | 0 | memory adj device and memory adj cell adj array.ti,ab,clm. and ((GaAs) adj substrate).ti,ab,clm. | US-PGPUB; USPAT; USOCCR; EPO; JPO; DERWENT | OR | ON | 2005/06/12 17:26 |

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| S73 | 0 | memory adj device and memory adj cell adj array.ti,ab,clm. and (GaAs AlGaAs) adj substrate.ti,ab, clm. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/06/12 17:27 |
| S74 | 0 | memory adj device and memory adj cell adj array.ti,ab,clm. and (SiGe SiC GaAs AlGaAs) adj substrate.ti,ab,clm. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/06/12 17:27 |
| S75 | 0 | memory adj device and memory adj cell adj array and (SiGe SiC GaAs AlGaAs) adj substrate.ti,ab, clm. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/06/12 17:27 |
| S76 | 45 | memory adj device and (SiGe SiC GaAs AlGaAs) adj substrate.ti,ab, clm. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/06/12 17:33 |
| S77 | 5 | memory adj device and (SiC) adj substrate.ti,ab,clm. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/06/12 17:34 |
| S78 | 39 | memory adj device and (GaAs) adj substrate.ti,ab,clm. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT | OR | ON | 2005/06/12 17:34 |
| S79 | 12 | config-dielectric | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/06/12 20:01 |